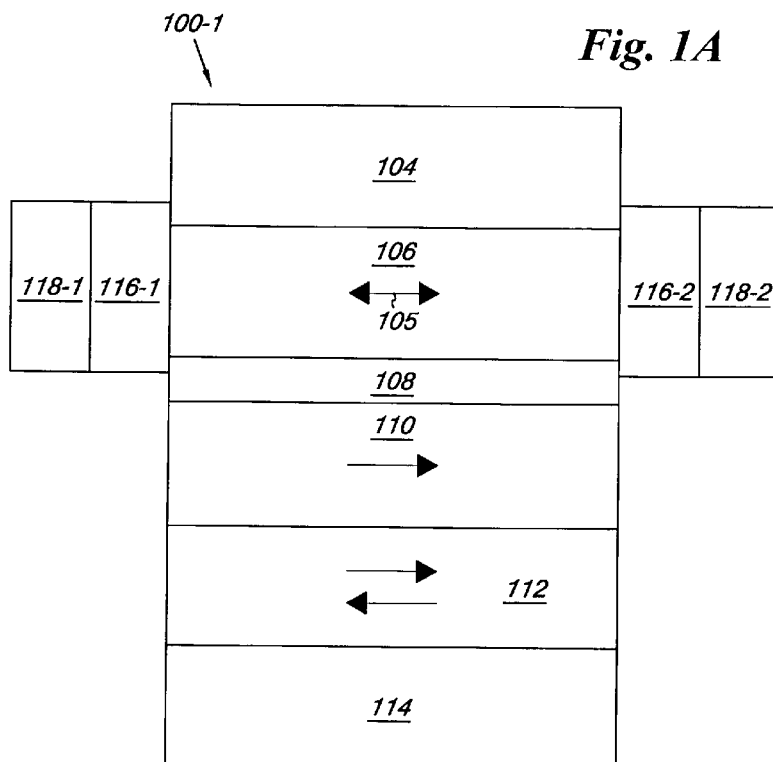




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(54) Title: SPIN TORQUE TRANSFER MEMORY CELL STRUCTURES AND METHODS



(57) Abstract: Spin Torque Transfer (STT) memory cell structures and methods are described herein. One or more STT memory cell structures include a tunneling barrier material positioned between a ferromagnetic storage material and a pinned ferromagnetic material in contact with an antiferromagnetic material and a multiferroic material in contact with the ferromagnetic storage material, wherein the antiferromagnetic material, the ferromagnetic storage material, and the pinned ferromagnetic material are located between a first electrode and a second electrode.



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